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CONFIRMATION

Jun. 10, 2002

SEMICONDUCTOR ENERGY LABORATORY CO., LTD.

ATTN : Ms. Miho KOMORI

Application No.: 90113144

Your ref.: TW4976/4978/4981/4982(T4792)

Our Case: 741062

Dear Sir:

This is in response to your fax dated May 27, 2002.

Enclosed please find the respect copies of Taiwanese Patent Nos. 251379 and 310478 in Chinese.

With respect to Taiwanese Patent No. 310478, we confirm that U.S. Patent 5,943,460 is a corresponding patent thereof by comparing the titles, inventors, assignees, and specifications (including claims and figures) of these two patents.

Finally, we translate the whole specification of Taiwanese Patent No. 251379 as follows:

The manufacture of TFT (Thin Film Transistor) on the glass is a popular solid-state element nowadays. Currently, the TFT manufactured by amorphous silicon (a-Si) has been used for the commercial Liquid Crystal Display (LCD) as a switching element. However, the carrier mobility of amorphous silicon is too low ($< 1 \text{ cm}^2/\text{V} \cdot \text{s}$), thus it can not be used for manufacturing the peripheral driving circuits. Since the TFT manufactured by polycrystalline silicon (poly-Si) has higher carrier mobility, it will compensate the shortcoming in this aspect and enhance the circuitry characters, product functions and cost efficiency if the poly-Si can be simultaneously manufactured on the glass. However, due to the temperature during the manufacturing process, the development of poly-Si TFT is restrained.

According to the conventional techniques for growing poly-Si thin film (for example, Low Pressure Chemical Vapor Deposition (LPCVD)), the temperature needs to be over 700°C in order to achieve good quality poly-Si. Even under the lower background pressure (such as 10^{-4} Torr) of the growing chamber, the growing chamber

needs to be over 600°C to achieve the poly-Si thin film with good crystallinity. Thus it is difficult to achieve growing on the low-cost glass. Besides, the transition temperature between polycrystalline silicon and amorphous silicon is 580°C, thus it is challenging and needs a breakthrough to grow poly-Si thin film below the temperature of 600°C. It has thus become a main object for the industry to develop the process of low temperature poly-Si. For the current techniques, the most common way is to grow amorphous silicon under about 550°C and go through the furnace annealing (about 550-600°C) for long period of time (generally 1-3 days), so that the poly-Si is obtained. Obviously, such a prolonged method is quite uneconomical, and the time required for the annealing process after ion implantation has not been included yet. So this method is not suitable for industrial production. A desired process is to directly grow good quality poly-Si thin film under low temperature without annealing and without ion implantation, so that the drain and source of low resistance may be obtained, which is accomplished by the present invention.

The main object of the present invention is to provide a simple and efficient process to directly grow the good quality poly-Si, poly-Ge, or poly-SiGe thin film under low temperature without ion implantation, so that the drain and source with excellent low resistance characteristics may be obtained for industrial production.

The present invention discloses a method for manufacturing poly-Si, poly-Ge, or poly-SiGe thin film transistor with low temperature, with the undoped poly-Si layer as a channel layer, by utilizing the methods of the ultrahigh vacuum chemical vapor deposition (UHV/CVD), the low pressure chemical vapor deposition (LPCVD), the molecular beam epitaxy (MBE), or the gas source MBE, especially by the ultrahigh vacuum chemical vapor deposition (UHV/CVD). Thus the good quality poly-Si (SiGe) thin film can be directly grown on a substrate (for example, glass substrate) under low temperature, without any annealing process, to obtain the drain and source with excellent low resistance characteristics, wherein the switch current is above 10^6 and the mobility of field effect electron hole is $28\text{cm}^2/\text{V} \cdot \text{sec}$. The process employed comprises: providing the undoped poly-Si layer as a channel layer, selectively etching upon the poly-Si to define poly-SiGe, growing high quality poly-Si and poly-SiGe thin film under low temperature by employing the growing method such as the ultrahigh vacuum chemical vapor deposition (UHV/CVD), growing under the extremely low growing pressure (about 1mtorr), and selectively etching the poly-SiGe with the $\text{HF}/\text{HNO}_3/\text{CH}_3\text{COOH}$ solution.

As the low pressure chemical vapor deposition is employed, the crystallinity of the thus grown poly-Si and the transition temperature thereof are deeply affected by the growing pressure. When growing is executed under an extremely low pressure, the

crystallinity can be significantly enhanced and the transition temperature thereof is further lowered, thus the poly-Si thin film can be grown on the substrate under low temperature (for example, lower than 600°C).

Furthermore, the present invention may also employ gas source MBE, to grow poly-Si thin film on the substrate under low temperature (for example, lower than 600 °C).

According to the elements to be formed, the processes of the methods for manufacturing the poly-Si, poly-Ge, or poly-SiGe TFT of the present invention are different, two examples are described as follows:

A. A method for manufacturing poly-Si, poly-Ge, or poly-SiGe thin film transistor above a gate, comprising:

providing the glass as a substrate, wherein said glass is normal glass; depositing low-resistance material above said glass to form a gate, wherein said low-resistance material is a high-temperature resistant metal such as chromium, tungsten, silicified metal; or doped poly-Si (Ge, SiGe); growing 500 °C low-temperature insulation layer (such as silicon oxide or silicon nitride layer) above said gate (2) as a gate dielectric layer; growing undoped poly-Si layer, then growing doped poly-SiGe layer above said poly-Si layer, under the low temperature of 550°C; selectively etching the poly-SiGe layer to form the source and the drain, wherein said selective etching is executed with HF/HNO₃/CH₃COOH solution (such a solution etches the poly-SiGe above the poly-Si with the 10 or more etching rate on the undoped poly-Si layer), and wherein said growing and doping processes is executed under extremely low growing pressure (about 1 mtorr). The doped element can be boron to form a p-type transistor, or can be phosphorous or arsenic to form an n-type transistor.

B. A method for manufacturing poly-Si, poly-Ge, or poly-SiGe thin film transistor under a gate, comprising:

providing the glass as a substrate; growing undoped poly-Si layer, then growing doped poly-SiGe layer, under the low temperature of 550°C; growing a 500°C low-temperature oxide layer to define the source and the drain area; selectively etching the low-temperature oxide layer above the doped poly-SiGe layer with the BOE solution; and then selectively etching the doped poly-SiGe layer above undoped poly-Si layer to form the source and the drain.

Next, growing the 500°C low-temperature insulation layer as a gate dielectric layer; depositing low-resistance gate material and defining its area, wherein said selective etching is executed with HF/HNO₃/CH₃COOH solution and the same growing pressure. The doped element can be boron to form a p-type transistor, or can be phosphorous or arsenic to form an n-type transistor.

The present invention will be described in the embodiments with reference to the following drawings.

Fig.1 is an illustrative diagram of the poly-Si TFT above the gate according to present invention.

Fig.2 is an illustrative diagram of the poly-Si TFT under the gate according to present invention.

Four embodiments of the present invention are described as follows:

Embodiment 1:

A method for manufacturing poly-Si thin film transistor above a gate (refer to Fig. 1) comprises the steps of : providing the glass as a substrate 1; depositing a high-temperature resistant and low-resistance metal or doped poly-Si (SiGe) above said glass to form a gate 2 and define the area thereof with the ultrahigh vacuum chemical vapor deposition method, under an extremely low growing pressure (about 0.94 mTorr) and background pressure about 10⁻⁸ Torr; growing a low-temperature insulation layer 3 above said gate 2 as a gate dielectric layer; wherein the thickness thereof is 30 - 100 nm; growing (under 500°C - 600°C) an undoped poly-Si layer 4, wherein the growing speed is about 0.66 nm/min and the thickness is 20 - 200 nm; then growing a poly-SiGe layer 5 doped with boron, phosphorous or arsenic, wherein the growing speed is about 2 nm/min and the thickness is 20 - 100 nm; selectively etching the poly-SiGe layer (above the poly-Si layer) to form the source and the drain with HF/HNO₃/CH₃COOH solution. The Si source adopted for deposition is SiH₄ or Si₂H₆ while the Ge source is GeH₄. Under such a low background pressure, the pollutant (such as oxygen) resolved in the deposited thin film will be far less than the lower limit (10¹⁷ atom/cm²) of the Second Ion Mass Spectroscopy (SIMS) measures.

Embodiment 2:

A method for manufacturing poly-Si thin film transistor under a gate (refer to Fig. 2), wherein the growing conditions and the Si and Ge sources adopted for deposition are the same as those of Embodiment 1, comprises the steps of : providing the glass as a substrate 1; growing an undoped poly-Si layer 2 of the

thickness 20 – 200 nm above said glass; then growing a poly-SiGe layer 3 (doped with boron, phosphorous or arsenic doped poly-SiGe layer) of the thickness 20 – 200 nm; growing a low-temperature oxide layer 4 of the thickness 200 – 300 nm to define the source and the drain area; etching the low-temperature oxide layer 4 above the poly-SiGe layer 3 with the BOE solution; and then selectively etching the poly-SiGe layer 3 above poly-Si layer 2 with $\text{HF}/\text{HNO}_3/\text{CH}_3\text{COOH}$ solution to form the source 3 and the drain 3; growing a low-temperature insulation layer 5 as a gate dielectric layer 5 of the thickness 30 – 100 nm; depositing the low-resistance gate material 6 (metal or doped poly-Si (SiGe)) and defining its area.

Embodiment 3:

Adopt the same growing steps and Si and Ge sources as those of Embodiment 1 and Embodiment 2 for manufacturing the TFTs above and under the gate, respectively. The growing method is changed to the low pressure chemical vapor deposition method, the growing pressure is changed as $10^{-2} \sim 10^{-3}$ Torr, and the background pressure is changed as 10^{-4} Torr. The low-temperature growing and doping temperature is now between 500°C and 600°C . The growing speeds for the poly-Si layer and the poly-SiGe layer are now about 1 nm/min and 2 nm/min, while the good quality poly-Si layer and poly-SiGe layer are still achieved. Since the higher background pressure is adopted, the vapor or oxygen in the growing chamber will somewhat cause the improper effect on the deposited thin films.

Embodiment 4:

Adopt the same growing steps and Si and Ge sources as those of Embodiment 1 and Embodiment 2 for manufacturing the TFTs above and under the gate, respectively. The growing method is changed to the gas source MBE method, the growing pressure is changed as 10^{-3} Torr, and the background pressure is changed as 10^{-10} Torr. The low-temperature growing and doping temperature is now between 500°C and 600°C . The growing speeds for the poly-Si layer and the poly-SiGe layer are now about 1 nm/min and 2 nm/min, while the good quality poly-Si layer and poly-SiGe layer are still achieved.

From the above description, it is understood that the present invention can directly grow good quality poly-Si (Ge, SiGe) thin films with a simple and efficient process, without employing the ion implantation method, so that the drain and source with excellent low resistance characteristics may be obtained for industrial production.

Any modification to the above embodiments can be made by any skilled person in the same field without getting beyond the scope of the attached claims.

Claims

1. A method for manufacturing poly-Si, poly-Ge, or poly-SiGe thin film transistor above a gate, comprising:
 - a) providing a glass substrate;
 - b) depositing low-resistance material above said substrate to form a gate;
 - c) growing low-temperature insulation layer above said gate as a gate dielectric layer;
 - d) growing undoped poly-Si, poly-Ge, or poly-SiGe layer above said gate dielectric layer with the ultrahigh vacuum chemical vapor deposition (UHV/CVD), the low pressure chemical vapor deposition (LPCVD) or the gas source MBE, under the temperature of 550°C or below;
 - e) growing doped poly-Si, poly-Ge, or poly-SiGe layer above said undoped poly-Si, poly-Ge, or poly-SiGe layer;
 - f) selectively etching said doped poly-Si, poly-Ge, or poly-SiGe layer above said undoped poly-Si, poly-Ge, or poly-SiGe layer to form the source and the drain.
2. The method according to claim 1, wherein said glass is normal glass.
3. The method according to claim 1, wherein said low-resistance material is a high-temperature resistant metal such as chromium, tungsten, silicified metal, etc., or doped poly-Si (Ge, SiGe alloy).
4. The method according to claim 1, wherein the thickness of said gate dielectric layer is 30 – 100 nm.
5. The method according to claim 1, wherein said grown undoped poly-Si, poly-Ge, or poly-SiGe layer has a thickness of 20 – 200 nm.
6. The method according to claim 1, wherein said grown doped poly-Si, poly-Ge, or poly-SiGe layer has a thickness of 20 – 200 nm.
7. The method according to claim 1, wherein said grown undoped poly-Si, poly-Ge, or poly-SiGe layer is a Si layer.
8. The method according to claim 1, wherein said grown undoped poly-Si, poly-Ge, or poly-SiGe layer is a Ge layer.

9. The method according to claim 1, wherein said grown undoped poly-Si, poly-Ge, or poly-SiGe layer is a SiGe layer.
10. The method according to claim 1, wherein said grown doped poly-Si, poly-Ge, or poly-SiGe layer is a Si layer.
11. The method according to claim 1, wherein said grown doped poly-Si, poly-Ge, or poly-SiGe layer is a Ge layer.
12. The method according to claim 1, wherein said grown doped poly-Si, poly-Ge, or poly-SiGe layer is a SiGe layer.
13. The method according to claim 1, wherein said selectively etching of said doped poly-SiGe layer above said undoped poly-Si layer is executed with $\text{HF}/\text{HNO}_3/\text{CH}_3\text{COOH}$ solution.
14. The method according to claim 1, wherein the growing method adopted in said step d) is the ultrahigh vacuum chemical vapor deposition (UHV/CVD) method.
15. The method according to claim 14, wherein the outer wall of the heating source is a hotwall when the ultrahigh vacuum chemical vapor deposition (UHV/CVD) method is adopted.
16. The method according to claim 14, wherein the Si source adopted for deposition is SiH_4 or Si_2H_6 while the Ge source is GeH_4 when the ultrahigh vacuum chemical vapor deposition (UHV/CVD) method is adopted.
17. The method according to claim 14, wherein said low-temperature insulation layer is grown under the temperature of 500°C or less, when the ultrahigh vacuum chemical vapor deposition (UHV/CVD) method is adopted.
18. The method according to claim 14, wherein the low-temperature growing and doping temperature is between 500°C and 600°C , when the ultrahigh vacuum chemical vapor deposition (UHV/CVD) method is adopted.
19. The method according to claim 14, wherein said growing and doping processes are executed under the extremely low growing pressure of about 1 mTorr and the background pressure of about 10^{-8} Torr, when the ultrahigh vacuum chemical vapor deposition (UHV/CVD) method is adopted.
20. The method according to claim 14, wherein said undoped poly-Si layer is grown with a growing speed of 0.66 nm/min, when the ultrahigh vacuum chemical vapor deposition (UHV/CVD) method is adopted.
21. The method according to claim 14, wherein said doped poly-SiGe layer is grown with a growing speed of 2 nm/min, when the ultrahigh vacuum chemical vapor deposition (UHV/CVD) method is adopted.
22. The method according to claim 1, wherein the growing method adopted in said step d) is the low pressure chemical vapor deposition (LPCVD) method.

23. The method according to claim 22, wherein the outer wall of the heating source is a hotwall when the low pressure chemical vapor deposition (LPCVD) method is adopted.
24. The method according to claim 22, wherein the Si source adopted for deposition is SiH_4 or Si_2H_6 while the Ge source is GeH_4 when the low pressure chemical vapor deposition (LPCVD) method is adopted.
25. The method according to claim 22, wherein said low-temperature insulation layer is grown under the temperature of 500°C or less, when the low pressure chemical vapor deposition (LPCVD) method is adopted.
26. The method according to claim 22, wherein the low-temperature growing and doping temperature is between 500°C and 600°C , when the low pressure chemical vapor deposition (LPCVD) method is adopted.
27. The method according to claim 22, wherein said growing and doping processes are executed under the extremely low growing pressure of about $10^{-2} \sim 10^{-3}$ Torr and the background pressure of about 10^{-4} Torr, when the low pressure chemical vapor deposition (LPCVD) method is adopted.
28. The method according to claim 22, wherein said undoped poly-Si layer is grown with a growing speed of 1 m/min and said doped poly-SiGe layer is grown with a growing speed of 2 m/min, when the low pressure chemical vapor deposition (LPCVD) method is adopted.
29. The method according to claim 1, wherein the growing method adopted in said step d) is the gas source MBE method.
30. The method according to claim 29, wherein the outer wall of the heating source is a coldwall when the gas source MBE method is adopted.
31. The method according to claim 29, wherein the Si source adopted for deposition is SiH_4 or Si_2H_6 while the Ge source is GeH_4 when the gas source MBE method is adopted.
32. The method according to claim 29, wherein said low-temperature insulation layer is grown under the temperature of 500°C or less, when the gas source MBE method is adopted.
33. The method according to claim 29, wherein the low-temperature growing and doping temperature is between 500°C and 600°C , when the gas source MBE method is adopted.
34. The method according to claim 29, wherein said growing and doping processes are executed under the extremely low growing pressure of about 10^{-3} Torr and the background pressure of about 10^{-10} Torr, when the gas source MBE method is adopted.
35. The method according to claim 1, wherein the ion with the valence of 3 is doped to

manufacture a p-type transistor.

36. The method according to claim 35, wherein said ion with the valence of 3 is the boron.

37. The method according to claim 1, wherein the ion with the valence of 5 is doped to manufacture an n-type transistor.

38. The method according to claim 37, wherein said ion with the valence of 5 is the phosphorous or arsenic.

39. A method for manufacturing poly-Si thin film transistor under a gate, comprising:

- a) providing a glass substrate;
- b) growing undoped poly-Si, poly-Ge, or poly-SiGe layer above said substrate with the ultrahigh vacuum chemical vapor deposition (UHV/CVD), the low pressure chemical vapor deposition (LPCVD) or the gas source MBE, under the temperature of 550°C or below;
- c) growing doped poly-Si, poly-Ge, or poly-SiGe layer above said undoped poly-Si, poly-Ge, or poly-SiGe layer under low temperature;
- d) growing low-temperature oxide layer above said doped poly-Si, poly-Ge, or poly-SiGe layer;
- e) etching the low-temperature oxide layer above the doped poly-Si, poly-Ge, or poly-SiGe layer with the BOE solution to define the source and the drain area;
- f) selectively etching the doped poly-Si, poly-Ge, or poly-SiGe layer above the undoped poly-Si, poly-Ge, or poly-SiGe layer to form the source and the drain;
- g) growing the low-temperature insulation layer as a gate dielectric layer;
and
- h) depositing the low-resistance gate material and defining its area.

40. The method according to claim 39, wherein said glass is normal glass.

41. The method according to claim 39, wherein said grown undoped poly-Si, poly-Ge, or poly-SiGe layer has a thickness of 20 – 200 nm.

42. The method according to claim 39, wherein said grown doped poly-Si, poly-Ge, or poly-SiGe layer has a thickness of 20 – 100 nm.

43. The method according to claim 39, wherein said grown low-temperature oxide layer has a thickness of 200 – 300 nm.

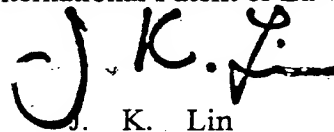
44. The method according to claim 39, wherein said grown low-temperature insulation layer as a gate dielectric layer has a thickness of 30 – 100 nm.
45. The method according to claim 39, wherein said grown undoped poly-Si, poly-Ge, or poly-SiGe layer is a Si layer.
46. The method according to claim 39, wherein said grown undoped poly-Si, poly-Ge, or poly-SiGe layer is a Ge layer.
47. The method according to claim 39, wherein said grown undoped poly-Si, poly-Ge, or poly-SiGe layer is a SiGe layer.
48. The method according to claim 39, wherein said grown doped poly-Si, poly-Ge, or poly-SiGe layer is a Si layer.
49. The method according to claim 39, wherein said grown doped poly-Si, poly-Ge, or poly-SiGe layer is a Ge layer.
50. The method according to claim 39, wherein said grown doped poly-Si, poly-Ge, or poly-SiGe layer is a SiGe layer.
51. The method according to claim 39, wherein said selectively etching of said doped poly-SiGe layer above said undoped poly-Si layer is executed with HF/HNO₃/CH₃COOH solution.
52. The method according to claim 39, wherein the ion with the valence of 3 is doped to manufacture a p-type transistor.
53. The method according to claim 52, wherein said ion with the valence of 3 is the boron.
54. The method according to claim 39, wherein the ion with the valence of 5 is doped to manufacture an n-type transistor.
55. The method according to claim 54, wherein said ion with the valence of 5 is the phosphorous or arsenic.

Abstract

A method for manufacturing poly-Si, poly-Ge, or poly-SiGe thin film transistor comprises the steps of: providing the glass as a substrate; depositing the high-temperature resistant and low-resistance metal or doped poly-Si (Ge, SiGe) above said glass to form a gate; growing a low-temperature insulation layer above said gate as a gate dielectric layer with a thickness of about 30 – 100 nm; growing undoped poly-Si, poly-Ge, or poly-SiGe layer with a thickness of about 20 – 200 nm, then growing doped poly-Si, poly-Ge, or poly-SiGe layer with a thickness of about 20 – 200 nm; selectively etching said doped poly-Si, poly-Ge, or poly-SiGe layer above said undoped poly-Si, poly-Ge, or poly-SiGe layer to form the source and the drain with HF/HNO₃/CH₃COOH solution.

Should you have any further questions, please do not hesitate to contact us.

Very Truly Yours,
Taiwan International Patent & Law Office

A handwritten signature in black ink, appearing to read 'J. K. Lin', with a stylized flourish at the end.

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010381128

WPI Acc No: 1995-282442/199537

XRAM Acc No: C95-127518

Prodn. of polysilicon, germanium or silicon-germanium thin film
transistor - under lower temperature and without the implantation

Patent Assignee: GYOSEIIN KOKKA KAGAKU IINKAI (GYOS-N); NAT SCI
COMMITTEE

(NASC-N)

Inventor: CHANG J; LIN H; LIN S

Number of Countries: 002 Number of Patents: 002

Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
TW 251379	A	19950711	TW 94100725	A	19940128	199537 B
JP 8023099	A	19960123	JP 9442274	A	19940314	199613 N

Priority Applications (No Type Date): TW 94100725 A 19940128; JP 9442274 A
19940314

Patent Details:

Patent No	Kind	Lan Pg	Main IPC	Filing Notes
TW 251379	A	20	H01L-021/331	
JP 8023099	A	5	H01L-029/786	

Abstract (Basic): TW 251379 A

Prodn. of polysilicon, Ge or Si-Ge thin film transistor with gate
on the down side includes: (a) supplying a glass as substrate; (b)
depositing the material with low resistance on the substrate to form
gate; (c) growing low-temperature insulator on the gate as gate
dielectric layer; (d) growing undoped polysilicon, Ge or Si-Ge layer on
gate dielectric layer with UHV/CVD, LPCVD or gas source MBE and below
550 deg. C; (d) growing doped polysilicon, Ge or Si-Ge layer on undoped
polysilicon, Ge or Si-Ge layer; and (e) selectively etching the doped
polysilicon, Ge or Si-Ge layer on the undoped polysilicon, Ge or Si-Ge
layer to form source and drain.

Dwg.0/2

Title Terms: PRODUCE; POLY; SILICON; GERMANIUM; SILICON; GERMANIUM;
THIN;

FILM; TRANSISTOR; LOWER; TEMPERATURE; IMPLANT

Derwent Class: L03; U11; U14

International Patent Class (Main): H01L-021/331; H01L-029/786

International Patent Class (Additional): H01L-021/336

File Segment: CPI; EPI

附件

公告本

251379

申請日期	83.1.28
案 號	83100725
類 別	1101L21/331

83年11月10日	修正 補充
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(以上各欄由本局填註)

發明專利說明書		
一、發明 名稱	中 文	多晶矽、銻、或矽銻薄膜電晶體之製造方法(83年11月修正本)
	英 文	
二、發明 創作人	姓 名	1. 張俊彥 3. 林孝義 2. 林鴻志
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三、申請人	姓 名 (名稱)	行政院國家科學委員會
	國 籍	中華民國
	住、居所 (事務所)	台北市和平東路二段106號18樓
	代 表 人 姓 名	郭南宏

經濟部中央標準局員工消費合作社印製

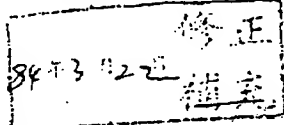
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本紙張尺度適用中國國家標準 (CNS) A4規格 (210×297公釐)

六、申請專利範圍



(第83100725號申請案申請專利範圍84年3月修正本)

1. 一種閘極在下之多晶矽、銻、或矽銻薄膜電晶體之製造方法，其包括：

- a) 提供一玻璃作為基板；
- b) 令低阻值之物質沉積於該基板形成閘極；
- c) 使於該閘極上成長低溫絕緣層做為閘極介電層；
- d) 以超高真空化學氣相沉積法(UHV/CVD)、低壓化學氣相沉積法(LPCVD)或氣相源分子束磊晶法(Gas Source MBE)於550℃以下，於該閘極介電層上成長未摻雜之多晶矽、銻、或矽銻層；
- e) 於該未摻雜之多晶矽、銻、或矽銻層上成長摻雜之多晶矽、銻、或矽銻層；以及
- f) 於該未摻雜之多晶矽、銻、或矽銻層上，選擇性蝕刻該摻雜多晶矽、銻、或矽銻層，形成源極與汲極(source and drain)。

2. 如申請專利範圍第1項所述之製造方法，其中該玻璃係一般常見之玻璃。

3. 如申請專利範圍第1項所述之製造方法，其中該低阻值之物質係耐高溫金屬(如鉻，鎢，矽化金屬等)或摻雜之多晶矽、銻、矽銻合金。

4. 如申請專利範圍第1項所述之製造方法，其中該閘極介電層其厚度為30-100nm。

5. 如申請專利範圍第1項所述之製造方法，其中該成長未摻雜之多晶矽、銻、或矽銻層，其厚度為20-200nm。

(請先閱讀背面之注意事項再填寫本頁)

訂

六、申請專利範圍

6. 如申請專利範圍第1項所述之製造方法，其中該再成長摻雜之多晶矽、銻、或矽銻層，其厚度為20-100nm。
7. 如申請專利範圍第1項所述之製造方法，其中該成長未摻雜之多晶矽、銻、或矽銻層係矽層。
8. 如申請專利範圍第1項所述之製造方法，其中該成長未摻雜之多晶矽、銻、或矽銻層係銻層。
9. 如申請專利範圍第1項所述之製造方法，其中該成長未摻雜之多晶矽、銻、或矽銻層係矽銻層。
10. 如申請專利範圍第1項所述之製造方法，其中該再成長摻雜之多晶矽、銻、或矽銻層係矽層。
11. 如申請專利範圍第1項所述之製造方法，其中該再成長摻雜之多晶矽、銻、或矽銻層係銻層。
12. 如申請專利範圍第1項所述之製造方法，其中該再成長摻雜之多晶矽、銻、或矽銻層係矽銻層。
13. 如申請專利範圍第1項所述之製造方法，其中該選擇性蝕刻摻雜之多晶矽銻層於未摻雜之多晶矽層上，係以HF/HNO₃/CH₃COOH完成之。
14. 如申請專利範圍第1項所述之製造方法，其中於該步驟(d)中所使用之成長方法係可為超高真空化學氣相沉積法(UHV/CVD)。
15. 如申請專利範圍第14項所述之製造方法，其中使用該超高真空化學氣相沉積法時，加熱源之外壁係為熱壁(hot wall)。

(請先閱讀背面之注意事項再填寫本頁)

訂

六、申請專利範圍

1 6 · 如申請專利範圍第 1 4 項所述之製造方法，其中使用該超高真空化學氣相沉積法時，所使用之矽源材 (Si source) 係為 SiH_4 或 Si_2H_6 ，鍺源材 (Ge source) 係為 GeH_4 。

1 7 · 如申請專利範圍第 1 4 項所述之製造方法，其中使用該超高真空化學氣相沉積法時，該低溫絕緣層係於低於 500°C 下成長。

1 8 · 如申請專利範圍第 1 4 項所述之製造方法，其中使用該超高真空化學氣相沉積法時，其低溫成長及摻雜溫度係介於 $500^\circ\text{C} \sim 600^\circ\text{C}$ 。

1 9 · 如申請專利範圍第 1 4 項所述之製造方法，其中使用該超高真空化學氣相沉積法時，該成長及摻雜過程係以極低成長壓力約 1mTorr 及背景壓力 10^{-8}Torr 下進行。

2 0 · 如申請專利範圍第 1 4 項所述之製造方法，其中使用該超高真空化學氣相沉積法時，係以 0.66nm/min 之成長速度，成長該未摻雜之多晶矽層。

2 1 · 如申請專利範圍第 1 4 項所述之製造方法，其中使用該超高真空化學氣相沉積法時，係以 2nm/min 之成長速度，成長該摻雜之多晶矽鍺層。

2 2 · 如申請專利範圍第 1 項所述之製造方法，其中於該步驟 (d) 中所使用之成長方法係可為低壓化學氣相沉積法 (LPCVD)。

(請先閱讀背面之注意事項再填寫本頁)

訂

六、申請專利範圍

2 3 · 如申請專利範圍第 2 2 項所述之製造方法，其中使用該低壓化學氣相沉積法時，加熱源之外壁係為熱壁(hot wall)。

2 4 · 如申請專利範圍第 2 2 項所述之製造方法，其中使用該低壓化學氣相沉積法時，所使用之矽源材(Si source)係為 SiH_4 或 Si_2H_6 ，鍺源材(Ge source)係為 GeH_4 。

2 5 · 如申請專利範圍第 2 2 項所述之製造方法，其中使用該低壓化學氣相沉積法時，該低溫絕緣層係於低於 500°C 下成長。

2 6 · 如申請專利範圍第 2 2 項所述之製造方法，其中使用該低壓化學氣相沉積法時，其低溫成長及摻雜溫度係介於 $500^\circ\text{C} \sim 600^\circ\text{C}$ 。

2 7 · 如申請專利範圍第 2 2 項所述之製造方法，其中使用該低壓化學氣相沉積法時，該成長及摻雜過程係以極低成長壓力約 $10^{-2} \sim 10^{-3} \text{ Torr}$ 及背景壓力約 10^{-4} Torr 下進行。

2 8 · 如申請專利範圍第 2 2 項所述之製造方法，其中使用該低壓化學氣相沉積法時，係以 1 m/min 之成長速度，成長該未摻雜之多品矽層以及以 2 m/min 之成長速度，成長該摻雜之多品矽鍺層。

2 9 · 如申請專利範圍第 1 項所述之製造方法，其中於該步驟(d)中所使用之成長方法係可為氣相源分子束磊晶法(Gas Source MBE)。

(請先閱讀背面之注意事項再填寫本頁)

訂

六、申請專利範圍

30．如申請專利範圍第29項所述之製造方法，其中使用該氣相源分子束磊晶法時，加熱源之外壁係為一冷壁(cold wall)。

31．如申請專利範圍第29項所述之製造方法，其中使用該氣相源分子束磊晶法時，所使用之矽源材(Si source)係為 SiH_4 或 Si_2H_6 ，鍺源材(Ge source)係為 GeH_4 。

32．如申請專利範圍第29項所述之製造方法，其中使用該氣相源分子束磊晶法時，該低溫絕緣層係於低於 500°C 下成長。

33．如申請專利範圍第29項所述之製造方法，其中使用該氣相源分子束磊晶法時，其低溫成長及摻雜溫度係介於 $500^\circ\text{C} \sim 600^\circ\text{C}$ 。

34．如申請專利範圍第29項所述之製造方法，其中使用該氣相源分子束磊晶法時，該成長及摻雜過程係以極低成長壓力約 10^{-3}Torr 及背景壓力約 10^{-10}Torr 下進行下進行。

35．如申請專利範圍第1項所述之製造方法，其中係摻雜三價之離子而製造成p-type電晶體。

36．如申請專利範圍第35項所述之製造方法，該三價之離子係硼。

37．如申請專利範圍第1項所述之製造方法，其中係摻雜五價之離子而製造成n-type電晶體。

(請先閱讀背面之注意事項再填寫本頁)

訂

六、申請專利範圍

38. 如申請專利範圍第37項所述之製造方法，該五價之離子係磷或砷。

39. 一種閘極在上之多晶矽薄膜電晶體之製造方法，其包括：

a) 提供一玻璃作為基板；

b) 以超高真空化學氣相沉積法(UHV/CVD)、低壓化學氣相沉積法(LPCVD)或氣相源分子束磊晶法(Gas Source MBE)於550°C以下，於該基板上成長未摻雜之多晶矽、銻、或矽銻層；

c) 使於該未摻雜之多晶矽、銻、或矽銻層上再低溫成長摻雜之多晶矽、銻、或矽銻層；

d) 使於該摻雜之多晶矽、銻、或矽銻層上再成長低溫氧化層；

e) 定義源極與汲極(source and drain)，先以BOE溶液於摻雜之多晶矽、銻、或矽銻層上蝕刻低溫氧化層；

f) 於未摻雜之多晶矽、銻、或矽銻層上選擇性蝕刻摻雜之多晶矽、銻、或矽銻層，使形成源極與汲極。

g) 成長低溫絕緣層，以作為閘極介電層；以及

h) 沉積低阻值之閘極材質並定義其區域。

40. 如申請專利範圍第39項所述之製造方法，其中該玻璃係一般常見之玻璃。

41. 如申請專利範圍第39項所述之製造方法，其中該成長未摻雜之多晶矽、銻、或矽銻層，其厚度為20 200 nm。

(請先閱讀背面之注意事項再填寫本頁)

訂

六、申請專利範圍

42. 如申請專利範圍第39項所述之製造方法，其中該再成長摻雜之多晶矽、銻、或矽銻層，其厚度為20-100nm。

43. 如申請專利範圍第39項所述之製造方法，其中該成長低溫氧化層，其厚度為200-300nm。

44. 如申請專利範圍第39項所述之製造方法，其中該成長低溫絕緣層，以作為閘極介電層其厚度為30-100nm。

45. 如申請專利範圍第39項所述之製造方法，其中該成長未摻雜之多晶矽、銻、或矽銻層係矽層。

46. 如申請專利範圍第39項所述之製造方法，其中該成長未摻雜之多晶矽、銻、或矽銻層係銻層。

47. 如申請專利範圍第39項所述之製造方法，其中該成長未摻雜之多晶矽、銻、或矽銻層係矽銻層。

48. 如申請專利範圍第39項所述之製造方法，其中該再成長摻雜之多晶矽、銻、或矽銻層係矽層。

49. 如申請專利範圍第39項所述之製造方法，其中該再成長摻雜之多晶矽、銻、或矽銻層係銻層。

50. 如申請專利範圍第39項所述之製造方法，其中該再成長摻雜之多晶矽、銻、或矽銻層係矽銻層。

51. 如申請專利範圍第39項所述之製造方法，其中該選擇性蝕刻摻雜之多晶矽銻層於未摻雜之多晶矽層上，係以 $\text{HF}/\text{HNO}_3/\text{CH}_3\text{COOH}$ 完成之。

(請先閱讀背面之注意事項再填寫本頁)

訂

六、申請專利範圍

5 2 . 如申請專利範圍第 3 9 項所述之製造方法，其中係摻雜三價之離子而製造成一 p - type 電晶體。

5 3 . 如申請專利範圍第 5 2 項所述之製造方法，該三價之離子係硼。

5 4 . 如申請專利範圍第 3 9 項所述之製造方法，其中係摻雜五價之離子而製造成一 n - type 電晶體。

5 5 . 如申請專利範圍第 5 4 項所述之製造方法，該五價之離子係磷或砷。

(請先閱讀背面之注意事項再填寫本頁)

訂

五、發明說明(1)

在玻璃上製造薄膜電晶體 (Thin Film Transistor, 簡稱 TFT), 乃現今非常熱門之一種固態元件, 目前利用非晶矽 (amorphous silicon, 簡稱 a-Si) 製成之 TFT 已被用於商業化之液晶顯示螢幕 (Liquid Crystal Display, 簡稱 LCD) 中作為開關切換元件, 然由於非晶矽之載子遷移率 (Carrier Mobility) 太低 ($< 1 \text{ cm}^2 / \text{V} \cdot \text{s}$), 故不能用於製作週邊之驅動電路, 然以多晶矽製成之薄膜電晶體, 則擁有較高之載子遷移率 ($> 10 \text{ cm}^2 / \text{V} \cdot \text{s}$), 故可彌補非晶矽薄膜電晶體在此方面之不足, 如能將多晶矽薄膜電晶體同時製造於玻璃上, 對電路特性, 產品功能及成本都有莫大之助益, 但由於在製程中溫度緣故, 限制了多晶矽薄膜電晶體在此方面之發展。

就傳統之成長多晶矽薄膜之技術 (如低壓化學氣相沉積法 LPCVD) 而言, 要獲得良好品質之多晶矽, 其溫度往往超過 700°C , 即使在較低之成長室的背景壓力如 10^{-4} Torr 為之, 仍必須在大於 600°C 之成長溫度下, 方能獲得結晶性良好之多晶矽薄膜, 故難以成長在低成本之玻璃上, 況且多晶矽與非晶矽之轉移溫度 (transition temperature) 的為 580°C , 要在 600°C 以下成長多晶矽薄膜, 極具挑戰性而有待突破, 所以需發展低溫化多晶矽之製程 ($< 600^\circ\text{C}$), 成為各方努力之方向, 就目前之技術而言, 最常為採用之方式, 乃首先於約 550°C 成長非晶矽, 而後經由長時間 (一般約 1-3 天) 之爐管退火處理 (約 $550-600^\circ\text{C}$), 使其晶化生成多晶矽, 很明顯, 此種曠日費時之方

(請先閱讀背面之注意事項再填寫本頁)

訂

一線

五、發明說明(2)

法甚不經濟，而且這還不包括離子佈植後之退火處理所需時間，故，此法不適合於工業上之生產。然較理想之製程即於低溫下直接成長良好品質之多晶矽薄膜，不必退火，同時不利用離子佈植的方法，即可獲致低阻值之汲極與源極(drain and source)，而本案即可達到上述之目的。

本案之主要目的為以一種簡單而有效率之製程，而可於低溫下直接成長良好品質之多晶矽、銻、或矽銻薄膜，同時不利用離子佈植的方法，即可獲致低阻值特性甚佳之汲極與源極，以適合工業上之生產。

本案為一種以低溫製造多晶矽、銻、或矽銻薄膜電晶體之製造方法，其主要觀念是以未摻雜之多晶矽層(undoped poly-Si layer)為通道層(channel layer)，其係利用超高真空化學氣相沉積法(UHV/CVD)、低壓化學氣相沈積法(LPCVD)、分子束磊晶法(MBE)，或氣相源分子束磊晶法(Gas Source MBE)，尤其是利用超高真空化學氣相沉積法(UHV/CVD)，故可於低溫下，於一基板上，如玻璃基板，直接成長良好品質之多晶矽(矽銻)薄膜，且不需任何之退火處理，即可獲致低阻值特性甚佳之汲極與源極，開關電流比大於 10^8 以上，場效電洞遷移率達 $28\text{cm}^2/\text{V}\cdot\text{sec}$ 。而其形成手段為令未摻雜之多晶矽層為通道層、於多晶矽上以選擇性蝕刻(selective etching)定義多晶矽銻、利用超高真空化學氣相沉積法(UHV/CVD)等成長方法低溫成長高品質poly-Si及poly-SiGe薄膜、以極低

五、發明說明(3)

成長壓力(約 1mtorr)下進行成長，利用 $\text{HF}/\text{HNO}_3/\text{CH}_3\text{COOH}$ 溶液選擇性蝕刻多晶矽銻。

若是採用低壓化學氣相沈積法，所成長多晶矽之結晶性及其轉變溫度(Transition Temperature)係深受成長壓力之影響，當在一極低壓力下成長，其結晶性可大幅提升而其轉變溫度會更加降低，因此亦可在低溫下(如低於 600°C 下)於基板上成長多晶矽薄膜。

另外，本案亦可採用氣相源分子束磊晶法(Gas Source MBE)，在低溫下(如低於 600°C 下)於基板上成長多晶矽薄膜。

本案多晶矽、銻、或矽銻薄膜電晶體之製造方法，然因欲形成之元件不同，而處理之程序亦有不同，現舉二例述之如下：

A. 閘極在下之多晶矽薄膜電晶體之製造方法；

以一玻璃作為基板，該玻璃為普通玻璃，令低阻值之物質，沉積於該玻璃形成閘極，而該低阻值之物質，係耐高溫之金屬如鉻，鎢，矽化金屬等或摻雜之多晶矽(銻、矽銻)，使於其上成長 500°C 低溫絕緣層(如氧化矽或氮化矽層)做為閘極介電層，續以 550°C 之低溫成長未摻雜之多晶矽層，再成長摻雜之多晶矽銻層，於該多晶矽層上，選擇性蝕刻多晶矽銻層，形成源極與汲極(source and drain)，該選擇性蝕刻係以 $\text{HF}/\text{HNO}_3/\text{CH}_3\text{COOH}$ 完成(此液蝕刻多晶矽銻於多晶矽上，對未摻雜多晶矽層之蝕刻率比可達 10 以上)，而其中該成長及摻雜過程係以極低成長壓力(約

五、發明說明(4)

1 m torr) 下成長。摻雜之元素可為硼而形成 p-type 電晶體，或可為磷、砷而形成 n-type 電晶體。

B. 閘極在上之多晶矽薄膜電晶體之製造方法：

以一玻璃作為基板，於其上以 550°C 之低溫成長未摻雜之多晶矽層，再成長摻雜之多晶矽鍍層，使於其上成長 500°C 低溫氧化層，定義源極與汲極區域，先以 BOE 溶液於摻雜之多晶矽鍍層上蝕刻低溫氧化層，再於未摻雜之多晶矽層上選擇性蝕刻摻雜多晶矽鍍層，使形成源極與汲極。

接著成長 500°C 低溫絕緣層，以作為閘極介電層，沉積低阻值之閘極材質並定義其區域，該選擇性蝕刻係以 HF/HNO₃/CH₃COOH 完成之，成長壓力亦然。摻雜之元素亦可為硼而形成 p-type 電晶體，或可為磷、砷而形成 n-type 電晶體。

為易於說明，本案得藉下述之較佳實施例及圖示以求更佳了解。

第一圖：係本案閘極在下多晶矽薄膜電晶體之示意圖。

第二圖：係本案閘極在上多晶矽薄膜電晶體之示意圖。

本案因欲形成之元件不同，而處理之程序亦有不同，現舉四較佳實施例述之如下：

實施例一：

一種閘極在下之多晶矽薄膜電晶體之製造方法，請參閱第一圖，其係以一玻璃作為基板 1，以極低成長壓力（約

五、發明說明(5)

0.94mTorr)及背景壓力約 10^{-8} Torr下並以超高真空化學氣相沉積法，於其上以耐高溫低阻值之金屬或摻雜之多晶矽(矽鍺)沉積於該玻璃形成閘極2，並定義其區域，使於其上成長低溫絕緣層3做為閘極介電層，其厚度為30-100nm，於約500~600℃下成長未摻雜之多晶矽層4，成長速度可約為0.66nm/min，其厚度為20-200nm，再成長摻雜硼、磷、或砷之多晶矽鍺層5，成長速度可約為2nm/min，其厚度為20-100nm，利用HF/HNO₃/CH₃COOH溶液，於多晶矽層上，選擇性蝕刻多晶矽鍺層，形成源極與汲極(source and drain)；於沈積時所使用之矽源材(Si source)係為SiH₄或Si₂H₆，鍺源材(Ge source)係為GeH₄，且由於在如此低之背景壓力下，沈積薄膜內所溶併之污染物，如氧氣之濃度將已遠低於二次離子質譜分析(Second Ion Mass Spectro Scopy SIMS)偵測度之下限(10^{17} 原子/cm²)。

實施例二：

一種閘極在上之多晶矽薄膜電晶體之製造方法，請參閱第二圖，成長條件及沈積時所使用之矽、鍺源材係同實施例一，其係以一玻璃作為基板1，於其上成長未摻雜之多晶矽層2，其厚度為20-200nm，再成長摻雜硼、磷、或砷之多晶矽鍺層3，其厚度為20-100nm，使於其上成長低溫氧化層4，其厚度為200-300nm，定義源極與汲極，先以BOE溶液於多晶矽鍺層3上蝕刻低溫氧化層4，再利用

五、發明說明(6)

HF/HNO₃/CH₃COOH溶液，於多晶矽層2上選擇性蝕刻多晶矽鍺層3，使形成源極3與汲極3，成長低溫絕緣層5，以作為閘極介電層5，其厚度為30-100nm，沉積低阻值之閘極材質6〔金屬或摻雜之多晶矽(矽鍺)〕並定義其區域。

實施例三：

成長步驟及矽、鍺源材同實施例一及二分別製造閘極在下及在上之薄膜電晶體，然成長方式改採低壓化學氣相沈積法，且成長條件中成長壓力改為 $10^{-2} \sim 10^{-3}$ Torr，背景壓力改為 10^{-4} Torr，低溫成長及摻雜溫度則係介於500℃~600℃間，以及多晶矽及矽鍺層之成長速度分別約為1nm/min及2nm/min時，仍可獲得良好之多晶矽及矽鍺層，但因採用較高之背景壓力，因此成長室內之水汽或氧氣會多少對沈積之薄膜造成不良影響。

實施例四：

成長步驟及矽、鍺源材同實施例一及二分別製造閘極在下及在上之薄膜電晶體，然成長方式改採氣相源分子束磊晶法(Gas Source MBE)，且成長條件中成長壓力為 10^{-3} Torr，背景壓力改為 10^{-10} Torr，低溫成長及摻雜溫度則係介於500℃~600℃間，以及多晶矽及矽鍺層之成長速度分別約為1nm/min及2nm/min時，仍可獲得良好之多晶矽及矽鍺層

由上之所述可知，本案確可以一種簡單而有效率之製程，於低溫下直接成長良好品質之多晶矽(鍺、矽鍺)薄膜，同時不利用離子佈植的方法，即可獲致低阻值特性甚佳之

五、發明說明(7)

汲極與源極，以適合工業上之生產，凡熟悉本技藝人士得任施匠思而為諸般修飾，然皆不脫如附申請專利範圍所欲保護者。

(請先閱讀背面之注意事項再填寫本頁)

訂

線

四、中文發明摘要(發明之名稱:)

多晶矽、銻、或矽銻薄膜電晶體之製造方法

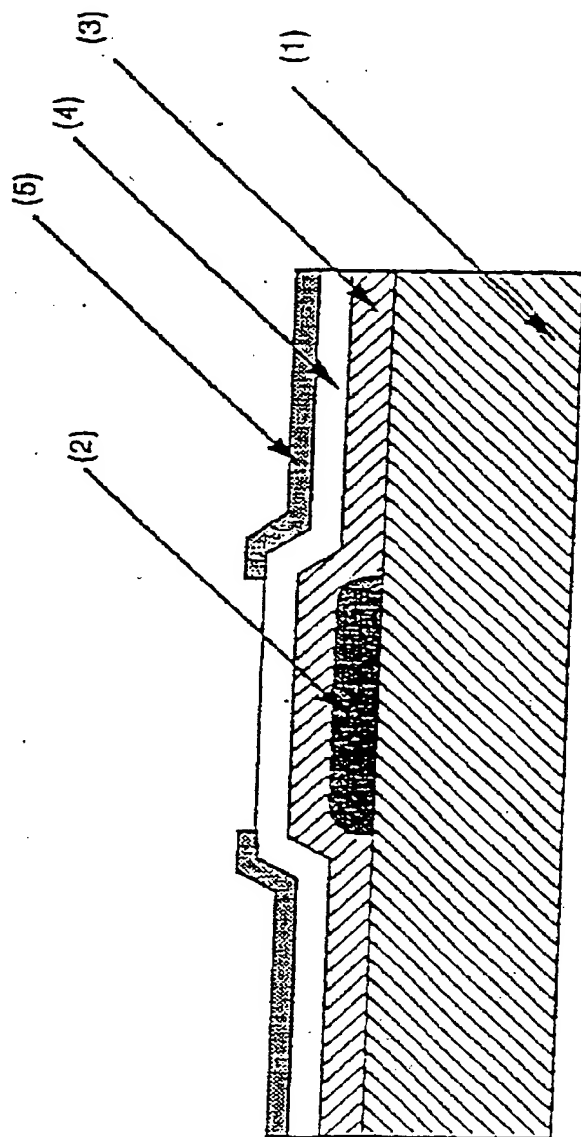
一種多晶矽、銻、或矽銻薄膜電晶體之製造方法，其係以一玻璃作為基板，次以耐高溫低阻值之金屬或摻雜之多晶矽(銻、矽銻)沉積於該玻璃形成閘極，再於其上使形成低溫絕緣層做為閘極介電層，其厚度約為30-100nm，再成長未摻雜之多晶矽、銻、或矽銻層，其厚度約為20-200nm，後再成長摻雜之多晶矽、銻、或矽銻層，其厚度約為20-100nm，然後利用HF/HNO₃/CH₃COOH溶液，於該未摻雜之多晶矽、銻、或矽銻層上，選擇性蝕刻該摻雜之多晶矽、銻、或矽銻層，以形成源極與汲極。

英文發明摘要(發明之名稱:)

251379

A8
B8
C8
D8

圖式



第一圖

(請先閱讀背面之注意事項再行繪製)

裝訂線

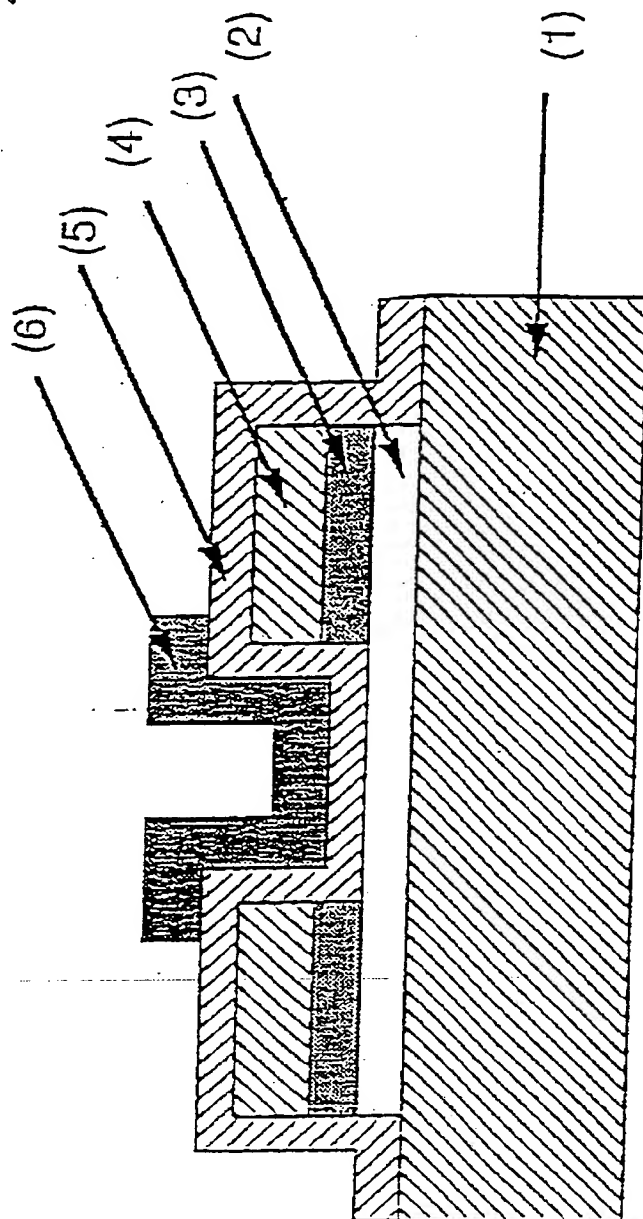
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251379

A8
B8
C8
D8

圖式



第二圖

(請先閱讀封面之注意事項再行繪製)

裝

訂

線

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